

## **AMENDMENTS TO THE SPECIFICATION**

Please delete the Abstract of the Disclosure and replace it with the following amended Abstract of the Disclosure:

The present invention relates to a synchronous self timed memory device. The device includes a plurality of memory cells forming a cell array, at least one local decoder interfacing with the cell array, at least one local sense amplifier and at least one local controller. The local sense amplifier interfaces with at least the decoder and cell array, and is adapted to precharge and equalize at least one line coupled thereto. The local controller interfaces with and coordinates the activities of at least the local decoder and sense amplifier. One embodiment of the present invention relates to a memory device comprising a plurality of synchronous controlled global elements and a plurality of self-timed local elements. In this embodiment, at least one of the ~~self-timed controlled~~ self-timed local elements interfaces with the synchronous controlled global element.